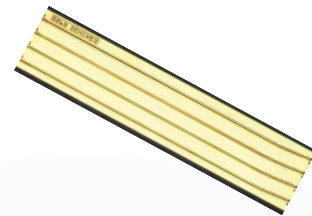


High Power RSOA 4-Emitter Chip



Part Number: CHPm-181

High Power 4 Emitters Gain Chip
Single-Mode RSOA
CW Wavelength at 1310nm covering O band



Features

- High Output Power
- High Dynamic Range
- High Efficiency
- 4 Emitters Mini Array
- Cost Effective

Application

- FMCW LiDAR
- Datacom
- Data Centers
- Telecom OTDR
- Telecom Optical Comm



SemiNex delivers the highest available power at infrared wavelengths between 12xx and 19xx nm. When necessary, we will further optimize the design of our InP & GaSb laser chips to meet our customers' specific optical and electrical performance needs. Diodes, bars and packages are tested to meet customer and market performance demands. Typical results and packaging options are shown. Contact SemiNex for additional details or to discuss your specific requirements.

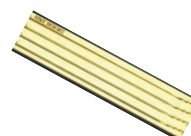
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High Power RSOA 4-Emitter Chip



Specification

CHPm-181



Optical	Symbol	Typ.	Units
Center Wavelength	λ_c	1310	nm
ASE Output Power @1A* per channel	P_{out}	0.2	Watts
Aperture Width	AW	4	μm
Number of Emitters		4	127 μm pitch
3dB Bandwidth	BW	80	nm
Beam Exit Angle	θ_{EXT}	19.5	degree
Polarization Extinction Ratio	PER	18	dB
Fast Axis Div.	$\theta_{\perp}$	30	deg FWHM
Slow Axis Div.	$\theta_{\parallel}$	16	deg FWHM
Front Facet Reflectivity		<0.1%	
Rear Face Reflectivity		98%	
Waveguide		Curved	
Electrical	Symbol		Units
Operating Current per channel	I_{op}	1	A
Operating Voltage	V_{op}	2	V
Mechanical		Range	Units
Chip Width		625	μm
Operating Temp.**		-20 to 75	$^{\circ}C$
Storage Temp.		-40 to 85	$^{\circ}C$

*Specified values are rated at a constant heat sink temperature of 20 $^{\circ}C$.

**High temperature operation will reduce performance and MTTF.
Unless otherwise indicated all values are nominal.

High Power RSOA 4-Emitter Chip



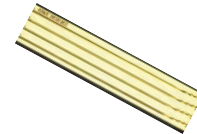
Mechanical Drawing

LASER RIDGE, PLANAR
WITH TOP SURFACE



CAVITY
LENGTH

0.0 P-SIDE FULLY METALIZED SURFACE
160.0 N-SIDE FULLY METALIZED SURFACE



CHIP ATTRIBUTES	
WAVELENGTH	1310nm $\pm$ 20nm
APERTURE WIDTH	4 μ m $\pm$ 1 μ m
EMITTER QTY	4
EMITTER PITCH	127 μ m $\pm$ 1 μ m
THICKNESS	160 μ m $\pm$ 10 μ m
CAVITY LENGTH	2.5mm $\pm$ 10 μ m

P-METAL		
MATERIAL	THICKNESS (nm)	TOLERANCE (nm)
Ti	50	$\pm$ 10
Pt	125	$\pm$ 25
Au	250	$\pm$ 50

N-METAL		
MATERIAL	THICKNESS (nm)	TOLERANCE (nm)
Ti	30	$\pm$ 10
Pt	125	$\pm$ 25
Au	400	$\pm$ 40

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